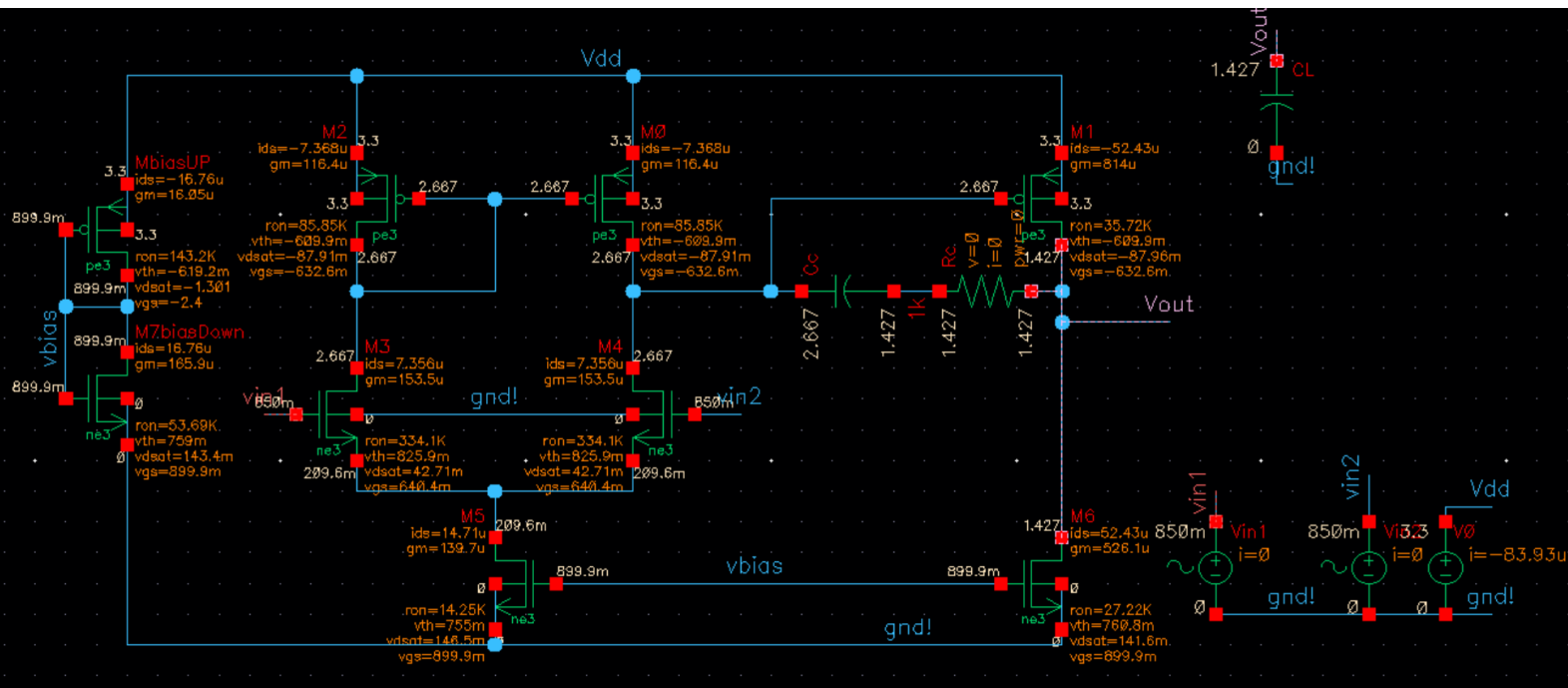


Two Stage Operational Amplifier

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Schematic (Before Layout)



$3.3 \times 89.93\mu = 296.769 \mu\text{W} \approx 297 \mu\text{W}$ much less than $500 \mu\text{W}$ as required.

$C_c = 2.5 \text{ pF} > 2.2 \text{ pF} = 0.22 \times C_L$ thus $\text{PM} > 60^\circ$

Also $V_{\text{bias}} = 899.9 \text{ mV} \approx 0.9 \text{ V}$

Transistor Properties

Library Name	PRIMLIB	off
Cell Name	ne3	value
View Name	symbol	off
Instance Name	M7biasDown	off

CDF Parameter	Value	Display
Model name	ne3	off
Voltage	3.6	off
Calculate Width Method	<input type="radio"/> FingerWidth <input checked="" type="radio"/> DeviceWidth	off
Model Limits	<input checked="" type="checkbox"/>	off
Device Width	2u M	off
Width per Finger	2u M	off
Length	360.0n M	off
Number of Fingers	1	off
Multiplier	1	off
m for Simulators	iPar ("m") * iPar ("ng")	off
Calculation Method	edit parasitics & callbacks off	off
Drain diffusion area	2.4e-13	off
Source diffusion area	2.4e-13	off
Drain diffusion periphery	1.96e-06	off
Source diffusion periphery	1.96e-06	off
Drain diffusion res squares	0.54	off
Source diffusion res squares	0.54	off

NMOS of bias circuit

Library Name	PRIMLIB	off
Cell Name	pe3	value
View Name	symbol	off
Instance Name	MbiasUP	off

CDF Parameter	Value	Display
Model name	pe3	off
Voltage	3.6	off
Calculate Width Method	<input type="radio"/> FingerWidth <input checked="" type="radio"/> DeviceWidth	off
Model Limits	<input checked="" type="checkbox"/>	off
Device Width	300n M	off
Width per Finger	300n M	off
Length	800n M	off
Number of Fingers	1	off
Multiplier	1	off
m for Simulators	iPar ("m") * iPar ("ng")	off
Calculation Method	callbacks enabled	off
Drain diffusion area	1.44e-13	off
Source diffusion area	1.44e-13	off
Drain diffusion periphery	1.56e-06	off
Source diffusion periphery	1.56e-06	off
Drain diffusion res squares	0.9	off
Source diffusion res squares	0.9	off

PMOS of bias circuit

This screenshot shows the Properties dialog for an NMOS transistor instance. The top section lists instance properties: Library Name (PRIMLIB), Cell Name (ne3), View Name (symbol), and Instance Name (M3). The bottom section, titled 'CDF Parameter', lists various physical and electrical parameters for the device.

Property	Value	Display
Library Name	PRIMLIB	off
Cell Name	ne3	value
View Name	symbol	off
Instance Name	M3	off

CDF Parameter	Value	Display
Model name	ne3	off
Voltage	3.6	off
Calculate Width Method	<input type="radio"/> FingerWidth <input checked="" type="radio"/> DeviceWidth	off
Model Limits	<input checked="" type="checkbox"/>	off
Device Width	172.000000u M	off
Width per Finger	172.000000u M	off
Length	350.0n M	off
Number of Fingers	1	off
Multiplier	1	off
m for Simulators	iPar("m")*iPar("ng")	off
Calculation Method	callbacks enabled	off
Drain diffusion area	8.256e-11	off
Source diffusion area	8.256e-11	off
Drain diffusion periphery	0.00034496	off
Source diffusion periphery	0.00034496	off
Drain diffusion res squares	0.00156977	off
Source diffusion res squares	0.00156977	off

NMOS of first stage

This screenshot shows the Properties dialog for a PMOS transistor instance. The top section lists instance properties: Library Name (PRIMLIB), Cell Name (pe3), View Name (symbol), and Instance Name (M0). The bottom section, titled 'CDF Parameter', lists various physical and electrical parameters for the device.

Property	Value	Display
Library Name	PRIMLIB	off
Cell Name	pe3	value
View Name	symbol	off
Instance Name	M0	off

CDF Parameter	Value	Display
Model name	pe3	off
Voltage	3.6	off
Calculate Width Method	<input type="radio"/> FingerWidth <input checked="" type="radio"/> DeviceWidth	off
Model Limits	<input checked="" type="checkbox"/>	off
Device Width	14.0u M	off
Width per Finger	14.0u M	off
Length	300n M	off
Number of Fingers	1	off
Multiplier	1	off
m for Simulators	iPar("m")*iPar("ng")	off
Calculation Method	callbacks enabled	off
Drain diffusion area	6.72e-12	off
Source diffusion area	6.72e-12	off
Drain diffusion periphery	2.896e-05	off
Source diffusion periphery	2.896e-05	off
Drain diffusion res squares	0.0192857	off
Source diffusion res squares	0.0192857	off

PMOS of first stage

This screenshot shows the Properties dialog for a current source instance. The top section lists instance properties: Library Name (PRIMLIB), Cell Name (ne3), View Name (symbol), and Instance Name (M5). The bottom section, titled 'CDF Parameter', lists various physical and electrical parameters for the device.

Property	Value	Display
Library Name	PRIMLIB	off
Cell Name	ne3	value
View Name	symbol	off
Instance Name	M5	off

CDF Parameter	Value	Display
Model name	ne3	off
Voltage	3.6	off
Calculate Width Method	<input type="radio"/> FingerWidth <input checked="" type="radio"/> DeviceWidth	off
Model Limits	<input checked="" type="checkbox"/>	off
Device Width	1.8u M	off
Width per Finger	1.8u M	off
Length	350.0n M	off
Number of Fingers	1	off
Multiplier	1	off
m for Simulators	iPar("m")*iPar("ng")	off
Calculation Method	callbacks enabled	off
Drain diffusion area	8.64e-13	off
Source diffusion area	8.64e-13	off
Drain diffusion periphery	4.56e-06	off
Source diffusion periphery	4.56e-06	off
Drain diffusion res squares	0.15	off
Source diffusion res squares	0.15	off

Current Source of first stage

Property	Value	Display
Library Name	PRIMLIB	off
Cell Name	ne3	value
View Name	symbol1	off
Instance Name	M6	off

CDF Parameter	Value	Display
Model name	ne3	off
Voltage	3.6	off
Calculate Width Method	<input type="radio"/> FingerWidth <input checked="" type="radio"/> DeviceWidth	off
Model Limits	<input checked="" type="checkbox"/>	off
Device Width	6u M	off
Width per Finger	6u M	off
Length	350.0n M	off
Number of Fingers	1	off
Multiplier	1	off
m for Simulators	iPar("m")*iPar("ng")	off
Calculation Method	callbacks enabled	off
Drain diffusion area	2.88e-12	off
Source diffusion area	2.88e-12	off
Drain diffusion periphery	1.296e-05	off
Source diffusion periphery	1.296e-05	off
Drain diffusion res squares	0.045	off
Source diffusion res squares	0.045	off

NMOS (Current source) of second stage

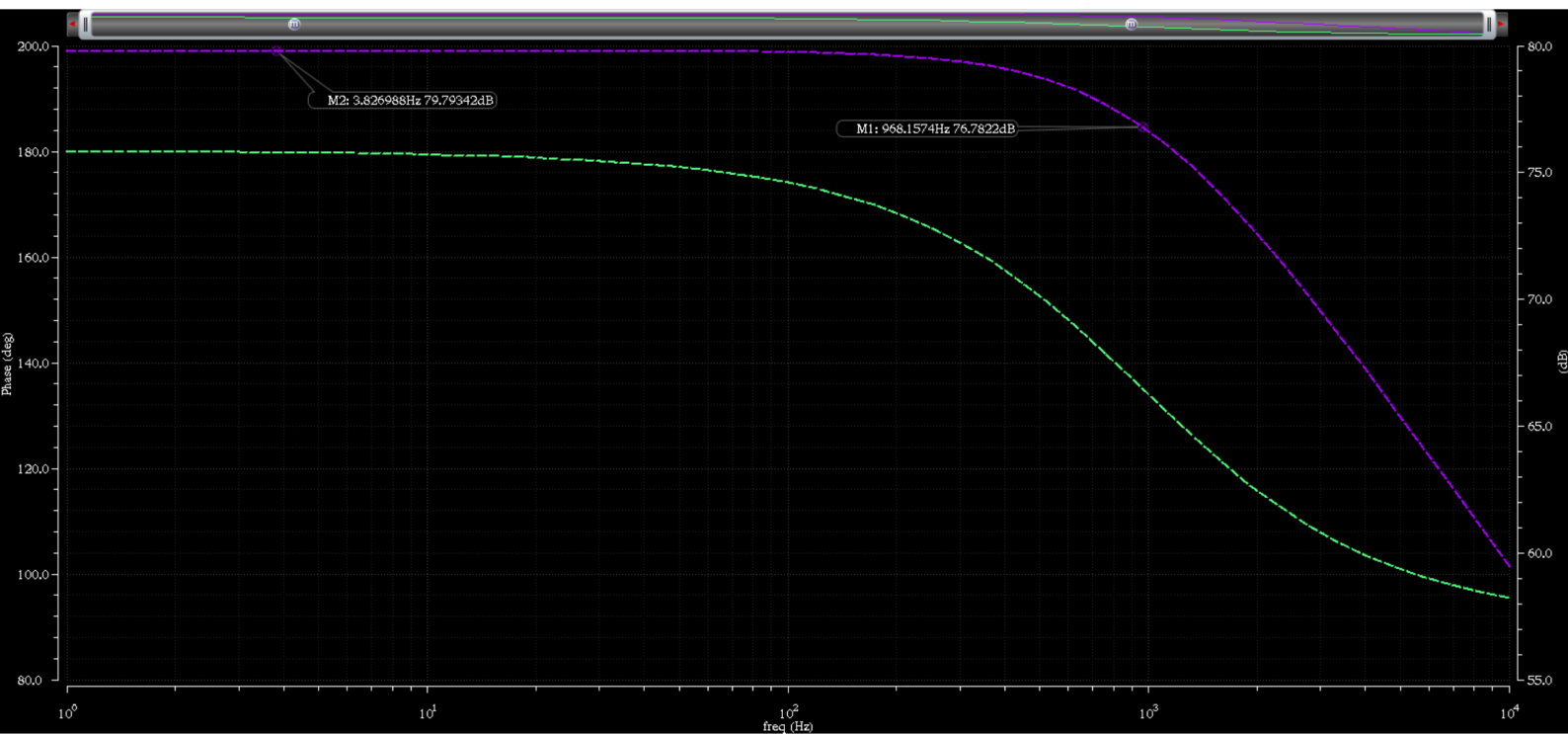
Property	Value	Display
Library Name	PRIMLIB	off
Cell Name	pe3	value
View Name	symbol1	off
Instance Name	M1	off

CDF Parameter	Value	Display
Model name	pe3	off
Voltage	3.6	off
Calculate Width Method	<input type="radio"/> FingerWidth <input checked="" type="radio"/> DeviceWidth	off
Model Limits	<input checked="" type="checkbox"/>	off
Device Width	84.0u M	off
Width per Finger	84.0u M	off
Length	300n M	off
Number of Fingers	1	off
Multiplier	1	off
m for Simulators	iPar("m")*iPar("ng")	off
Calculation Method	callbacks enabled	off
Drain diffusion area	4.032e-11	off
Source diffusion area	4.032e-11	off
Drain diffusion periphery	0.00016896	off
Source diffusion periphery	0.00016896	off
Drain diffusion res squares	0.00321429	off
Source diffusion res squares	0.00321429	off

PMOS of second stage

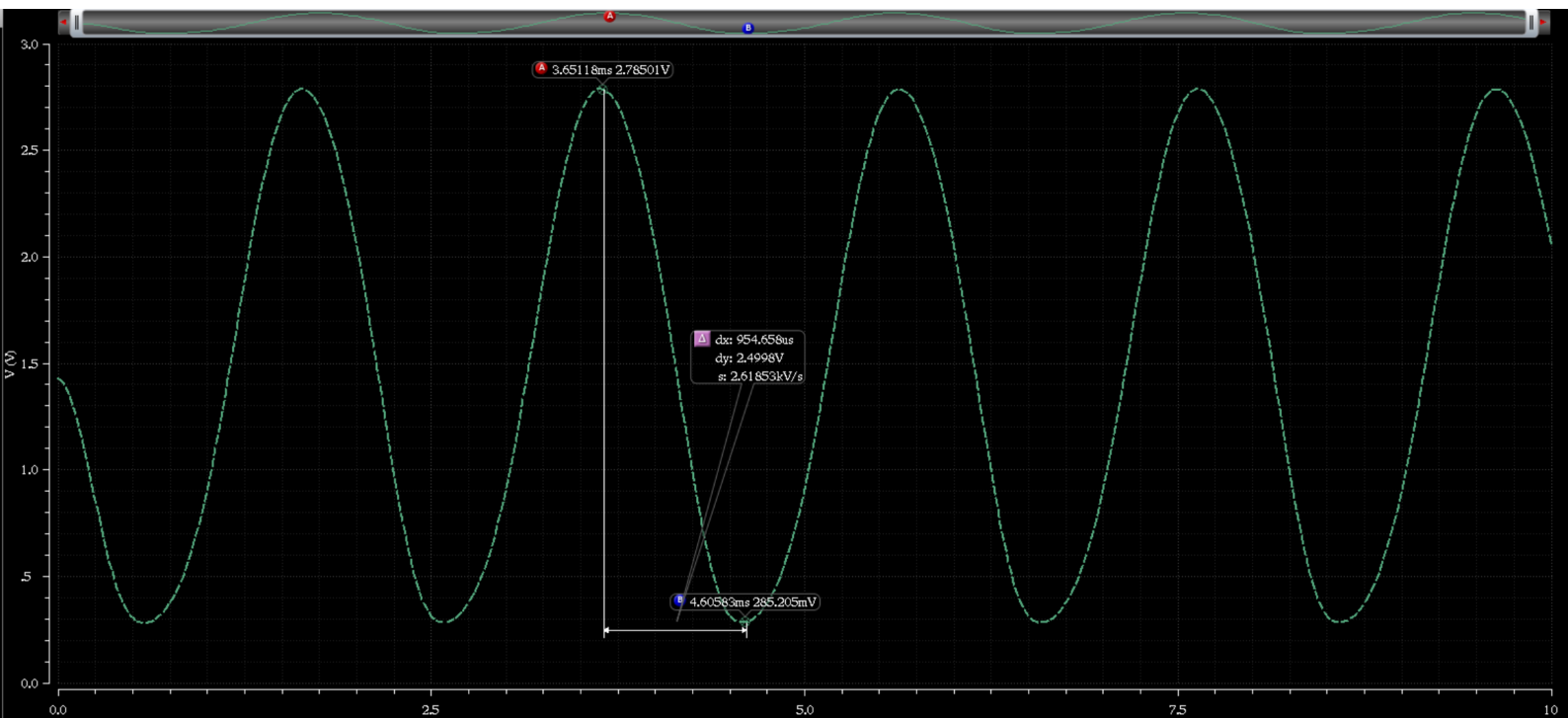
Note: Number of fingers will be selected with layout design.

Simulation Results

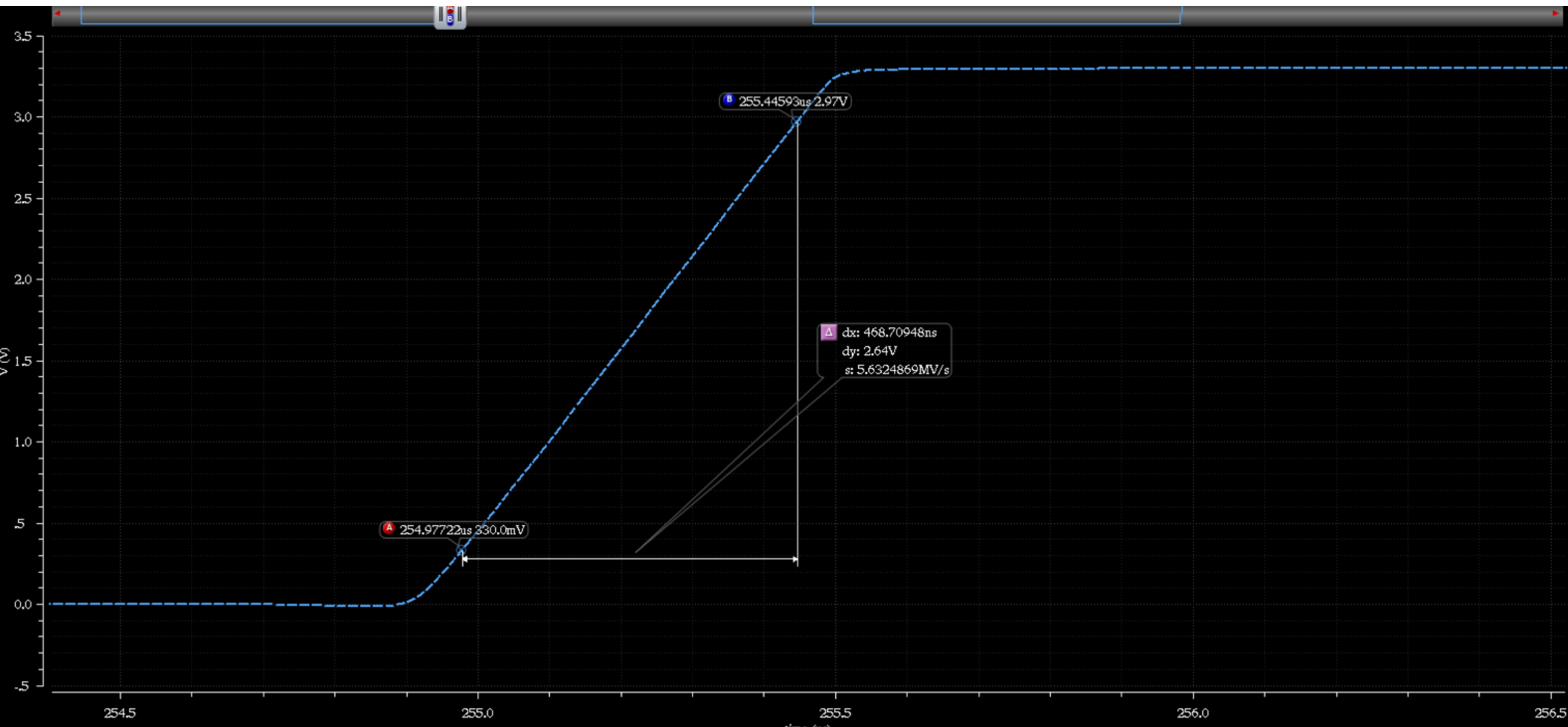


$A_v \approx 79.79\text{dB}$ (9764.97), which is slightly lower ($\sim 2.35\%$) than required.

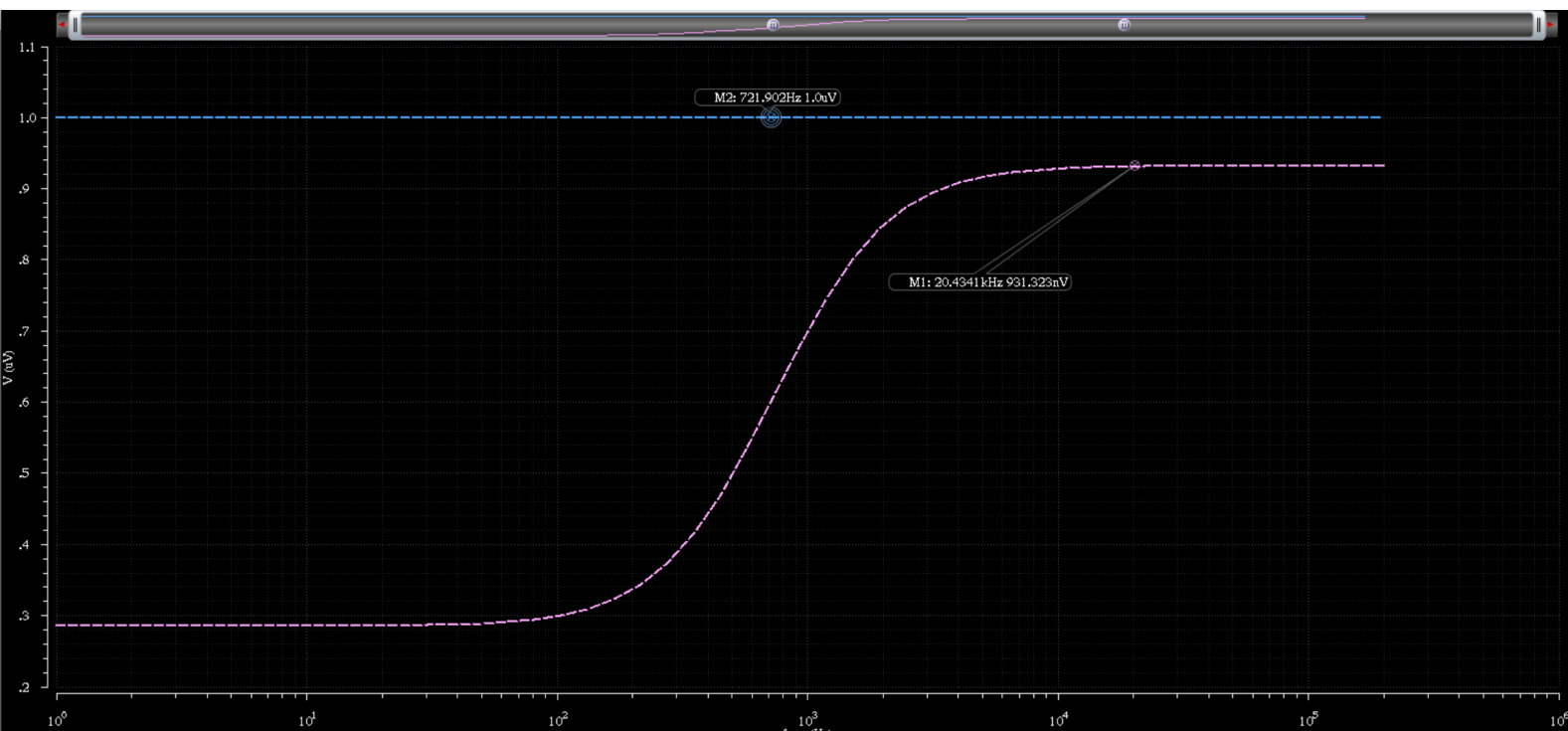
$f_{\text{upper}3\text{dB}} \approx 968.16\text{ Hz}$ thus Gain Bandwidth $\approx 9.45\text{ MHz}$, which is lower ($\sim 5.46\%$) than required.



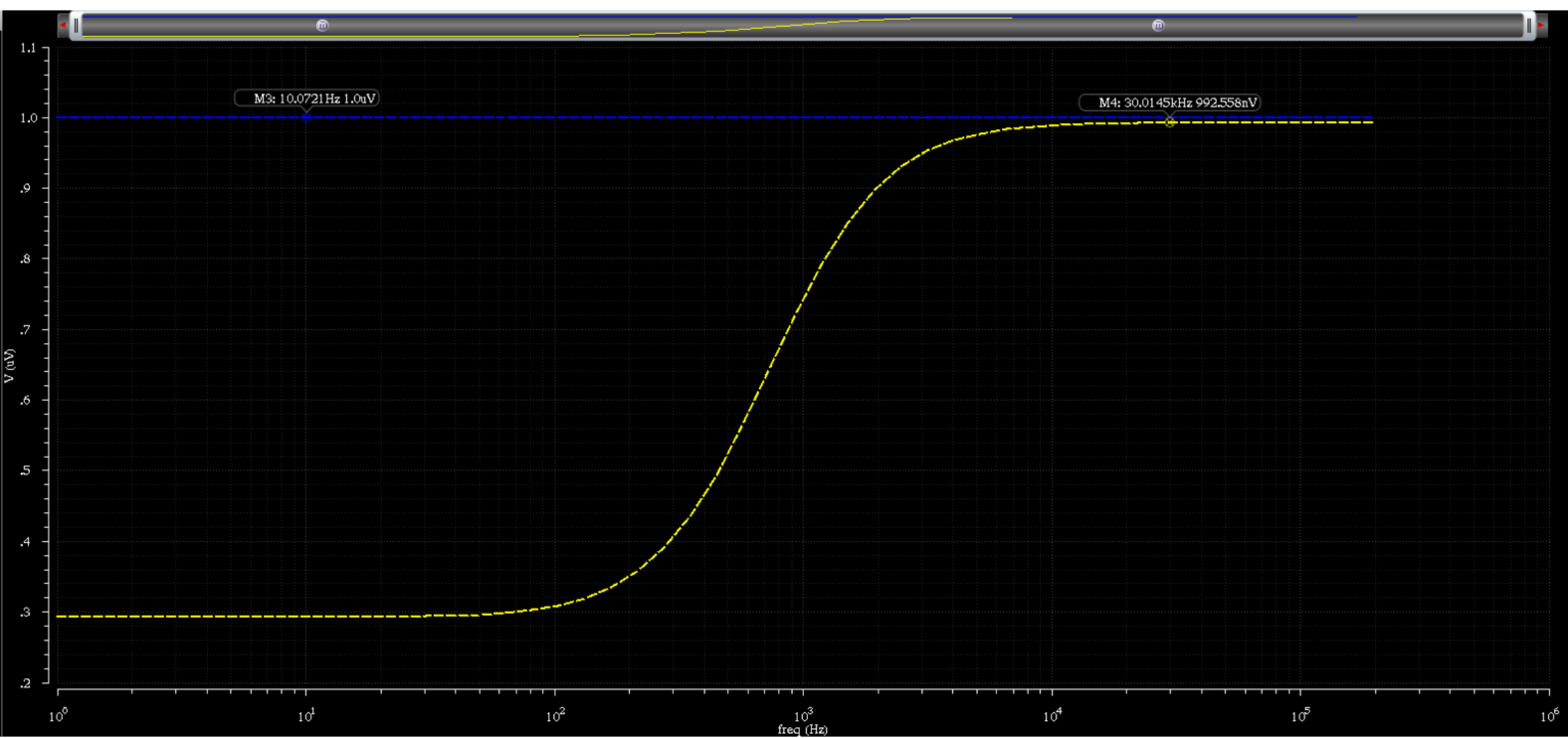
I was able to obtain output voltage swing of $\sim 2.5\text{ V}$



Slew rate $\approx 5.63 \text{ MV/s} = 5.63 \text{ V}/\mu\text{s}$ as higher (12.6%) than required



By applying small AC voltage to V_{dd} I calculated $\text{PSRR}_{dd} = 20 \cdot \log(A_v/A_{dd})$
 From simulation results $A_{dd} \approx 0.931$ thus $\text{PSRR}_{dd} \approx 80.411 \text{ dB}$



By applying small AC voltage after ground I calculated $PSRR_{ss} = 20 \cdot \log(A_v/A_{ss})$

From simulation results $A_{ss} \approx 0.992$ thus $PSRR_{ss} \approx 79.858$ dB

Note: Since our design does not contain V_{ss} I used ground node.

Topology:

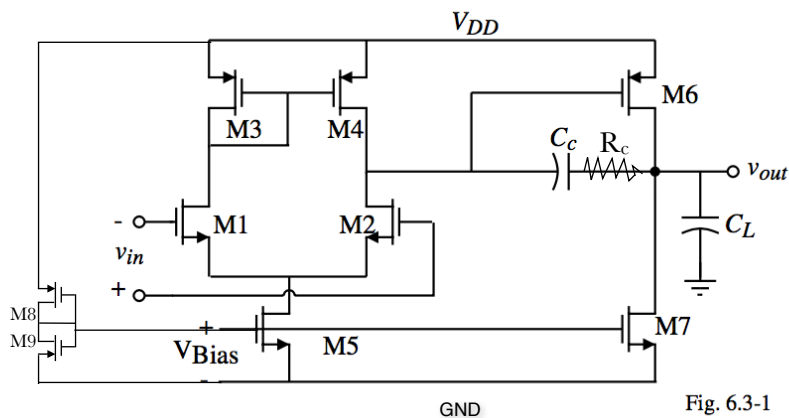


Fig. 6.3-1

My op-amp has three circuits. First one contains M8 and M9 transistors. These transistors are diode connected thus show ohmic behaviour and used as a voltage divider to provide necessary bias voltage to M5 and M7 transistors (current sources). Second circuit is first stage of op-amp, differential amplifier. Differential stage offers high gain and good noise handling as we see at previous lab assignment. Last circuit is second stage of op-amp, common source amplifier with active current source load. Common source stage provided large output swing.

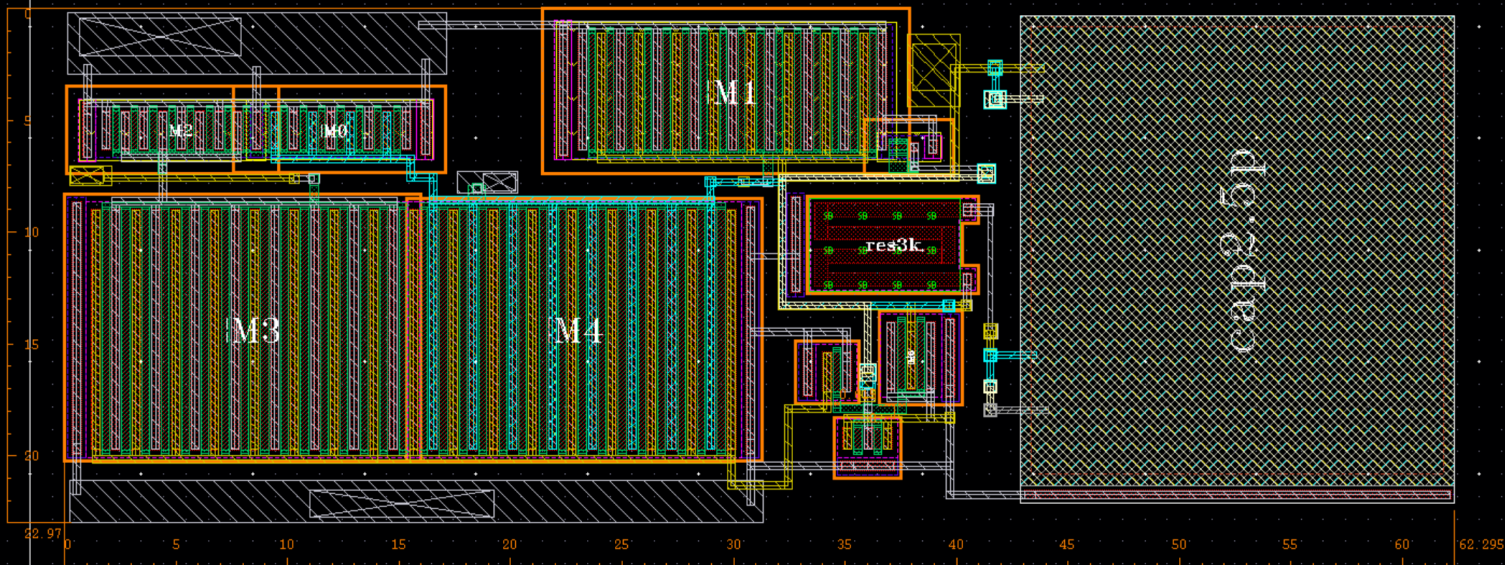
Hand Calculations: (all subscripts refer to Fig. 6.3-1, not schematic)

- I select $V_{inDC} = 0.9$ V (later decreased it 0.85 V to increase gain)
- I started my calculations with C_c . Since $C_L = 10$ pF, $0.22 \times C_L = 2.2$ pF. Thus for $PM > 60^\circ$ $C_c > 2.2$ pF. I choose $C_c = 2.5$ pF.
- I calculate $I_{5min} = SR \times C_c$. For $SR > 5$ V/ μ s $I_5 > 12.5$ μ A thus $I_4 = I_3 > 6.25$ μ A. I choose $I_5 \approx 15$ μ A. (Note that $I_7 \gg I_5$)
- For $P < 500$ μ W $I_{DDmax} = 151.51$ μ A. I choose $I_{biascircuit} \approx 25$ μ A thus $I_7 \approx 100$ μ A.
- I calculate W/L ratios of bias transistors using formula $\mu_{cox}(W/L)V_{gs} = I_d$, equalising I_{ds} and $V_{Bias} \approx 0.9$ V. Later I increased L values for lower $I_{biascircuit}$.
- I calculate gm_{1min} from $gm_1 = C_c \times GBW$, $gm_1 > 25$ $\mu(\Omega^{-1})$
- $((W/L)_5 / (W/L)_7) = I_5 / I_7 \approx 0.15$
- Later I put my calculations into schematics and simulate. I had to adjust my transistor sizes to increase gain and put $V_{outDC} \approx 1.5$ V for better voltage swing.

Conclusion (Before layout):

With two stage op-amp we were able to obtain very high gain (~ 80 dB) with bandwidth of ~ 1 kHz. To be able to obtain this much gain, I had to use huge transistors (172 μ and 84 μ). On the other hand I was able to work with low power (~ 300 μ W) while satisfying Slew rate requirement (~ 5.6 V/ μ s). My amplifier provides good power supply rejection ratio for both V_{DD} and V_{SS} (ground) (both ~ 80 dB), if I calculate them correctly. I was able to obtain ~ 2.5 V voltage swing with a little distortion at minimum value and ~ 3 V voltage swing with a little distortion at maximum value and some distortion at minimum value (signal is still in sine shape). I had to adjust results of my calculations a lot to get my design working, like previous labs. My initial values and adjusted Width values are different.

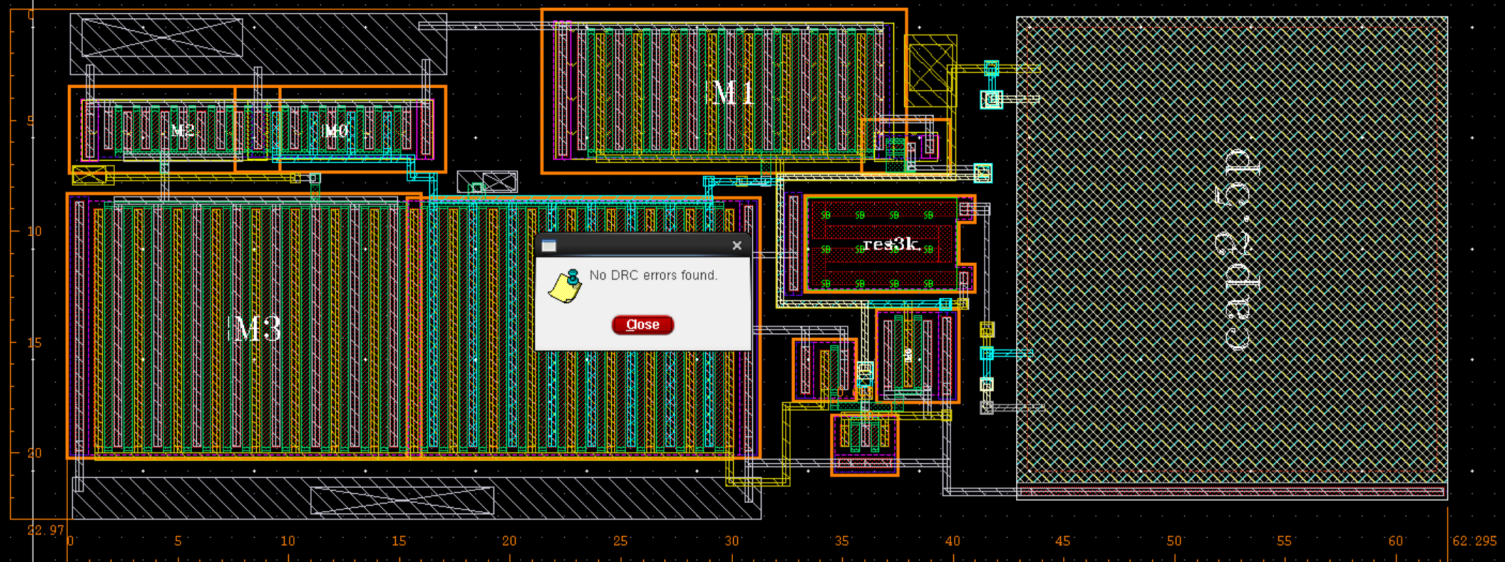
First Layout:

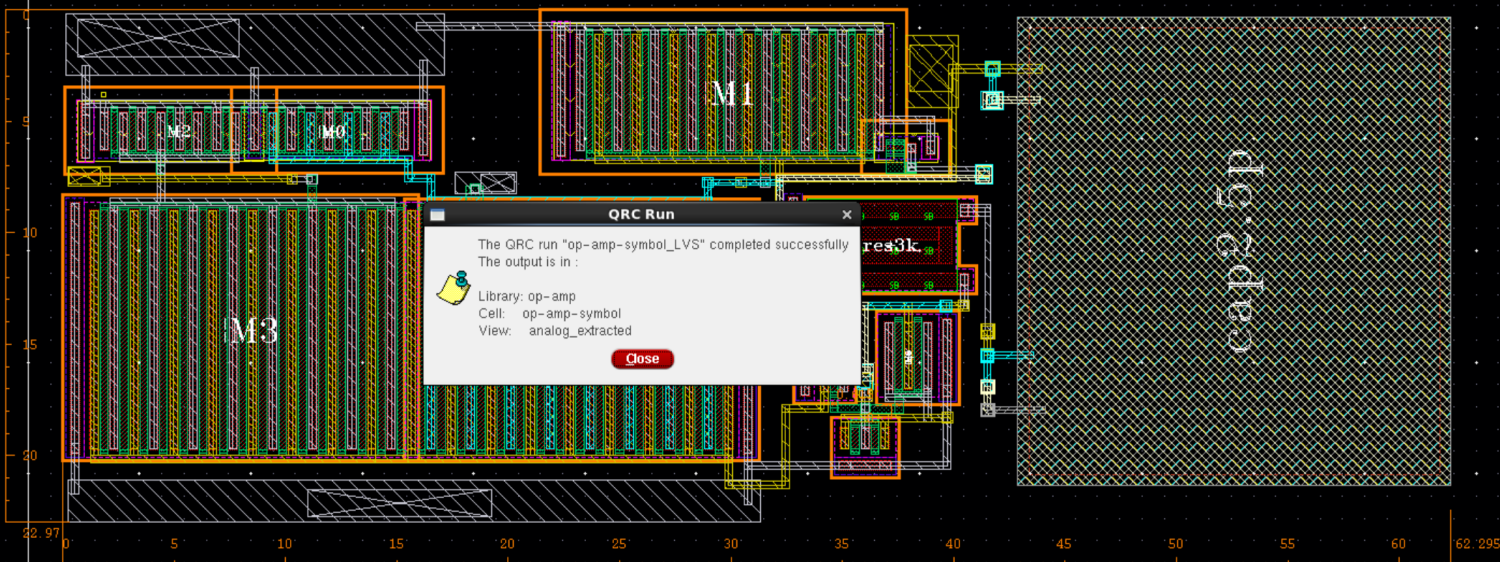
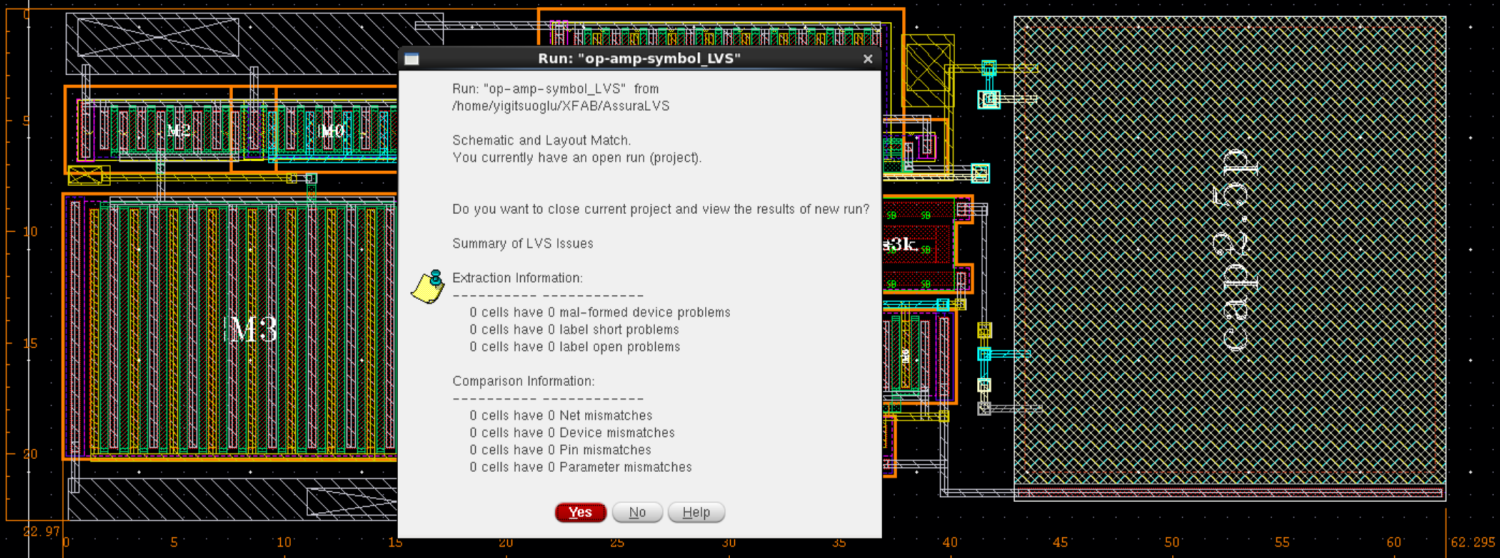


I was able to fit my design in 29.97 x 62.295 rectangle

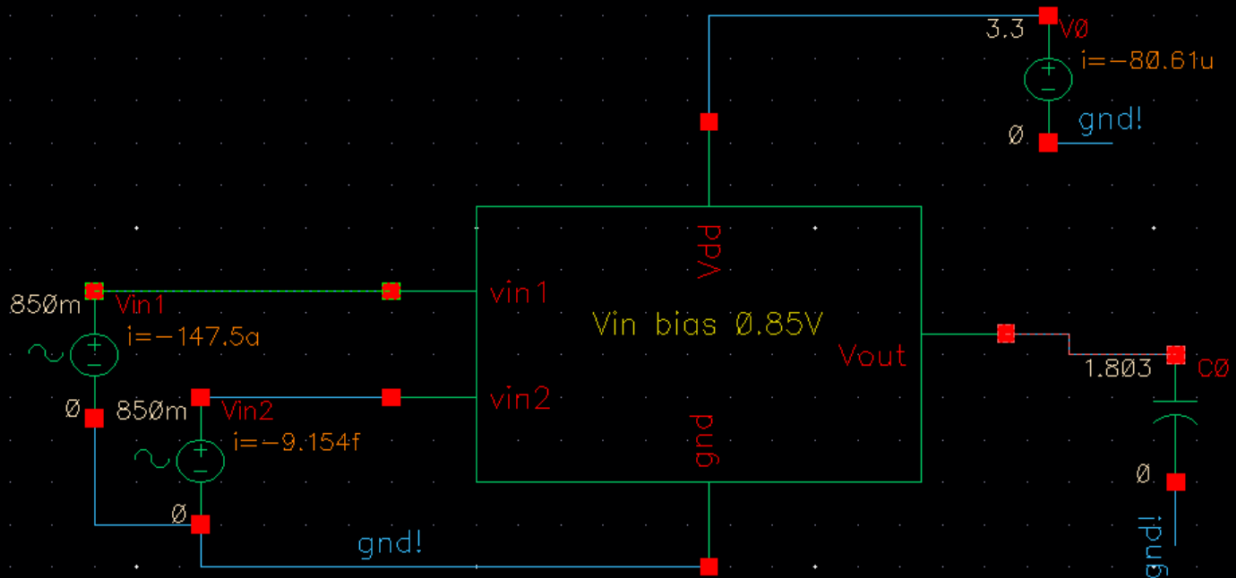
Note: I change the order of capacitor and resistor

DRC, LVS and QRC (First)



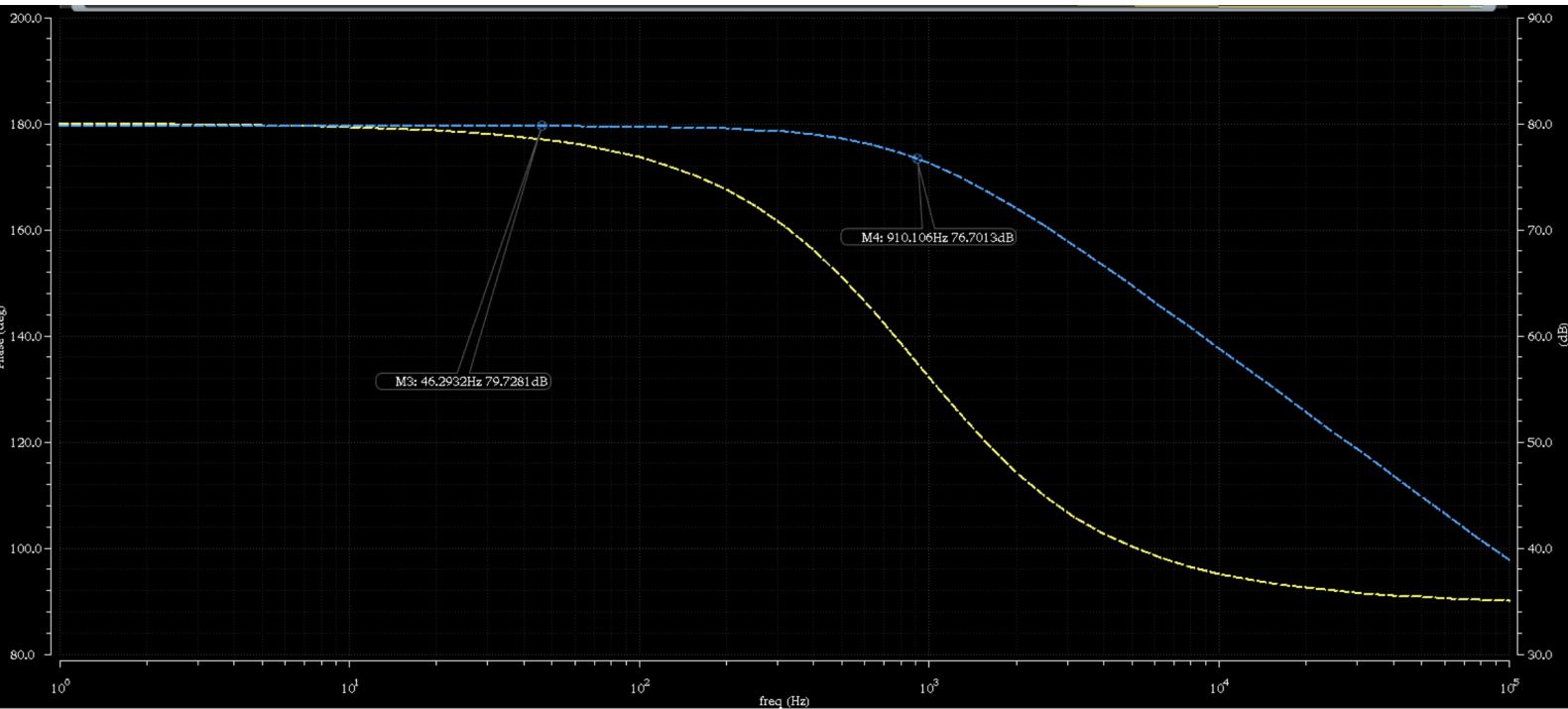


Schematic (After First Layout)

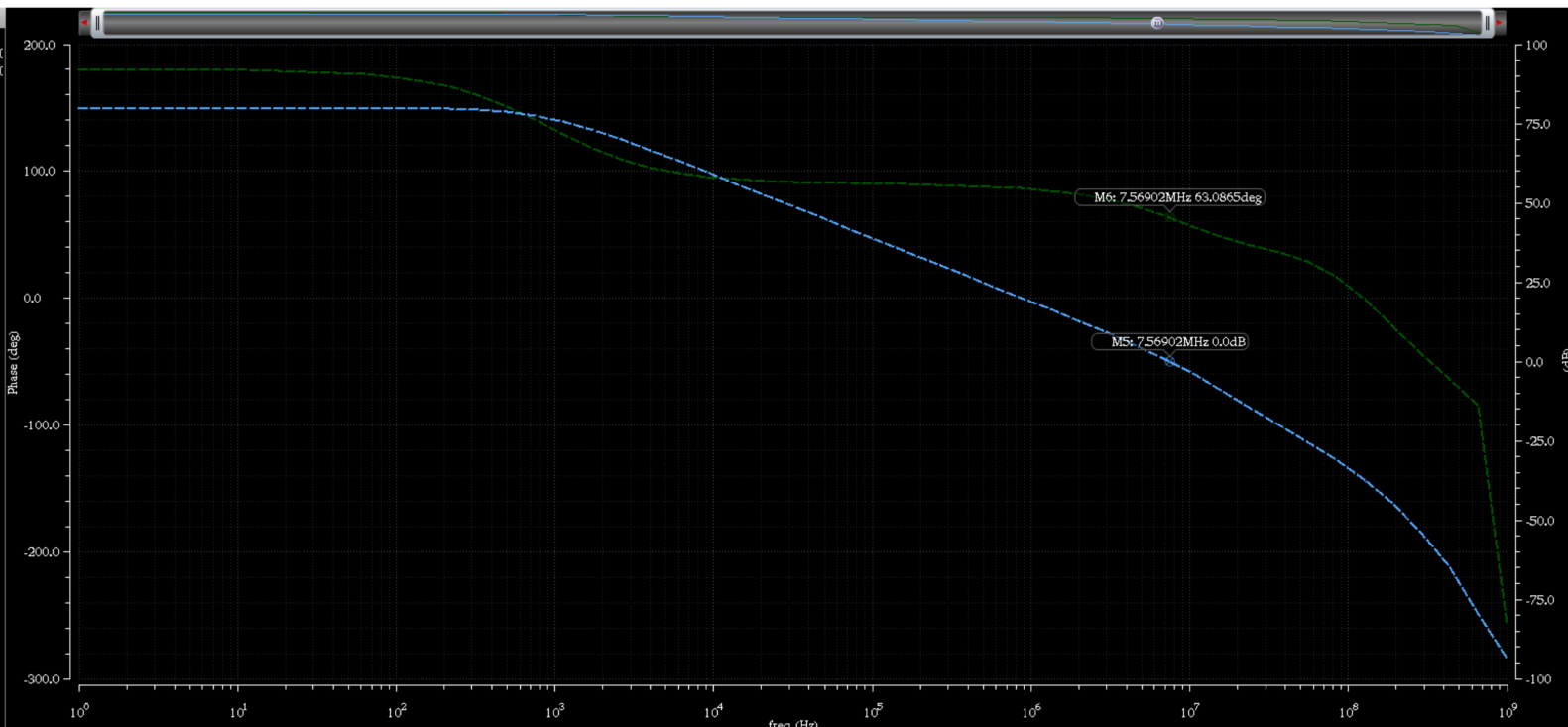


After layout W_{tot} decreased to $\sim 266 \mu W$, nearly half of maximum value
 V_{outDC} increased to $\sim 1.8 V$

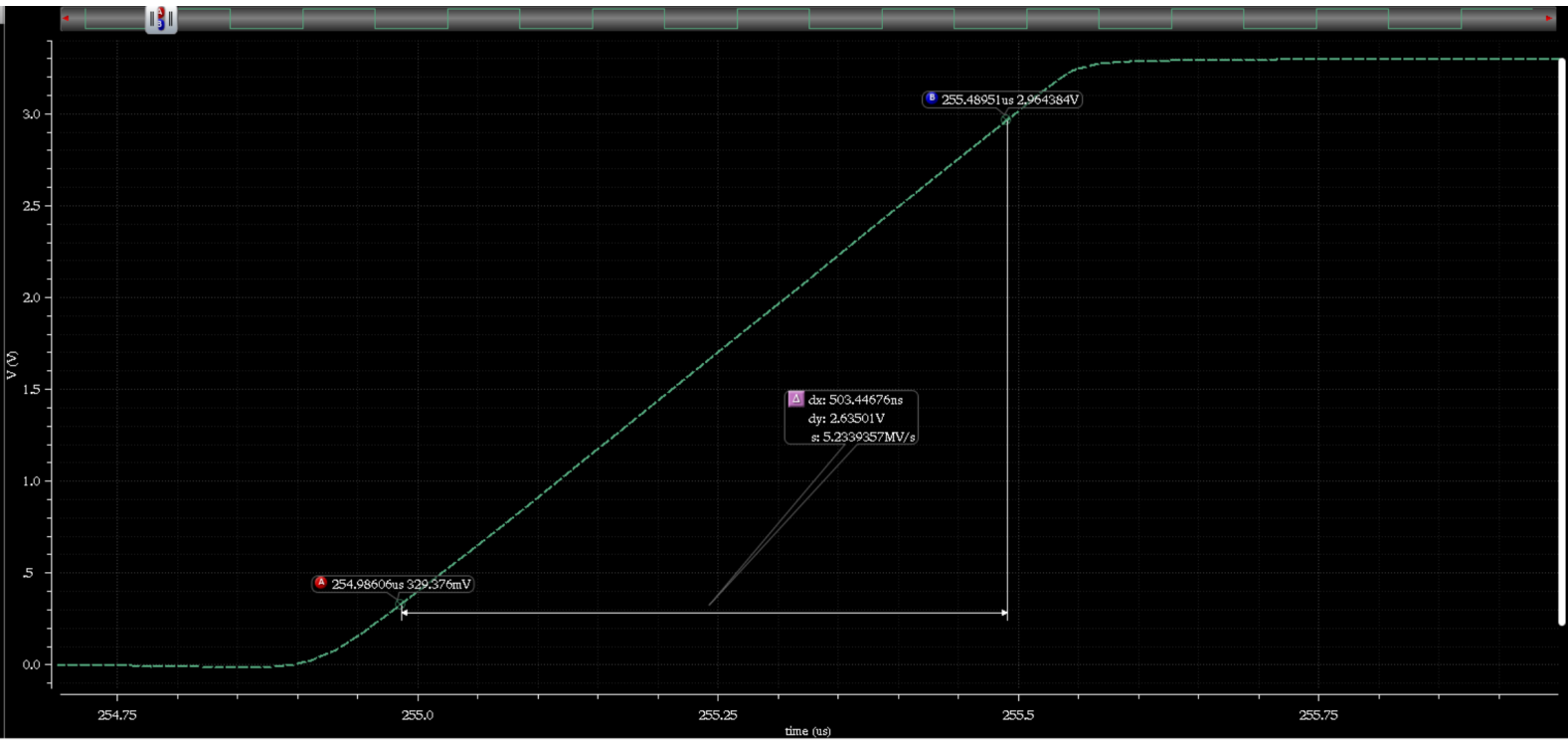
Simulation Results (After First Layout)



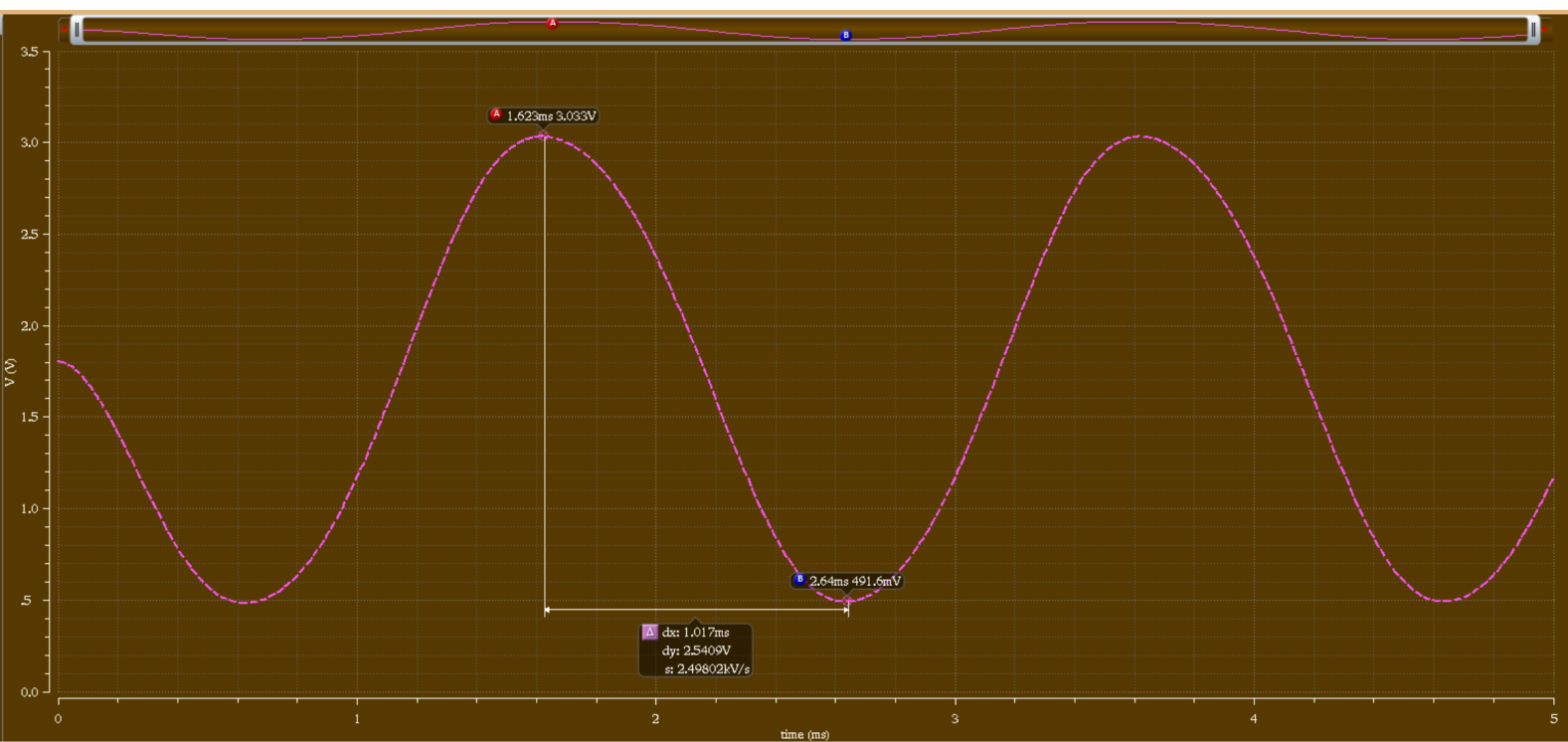
A_v decreased to ~ 79.73 dB, ~ 96939.3 V/V which is $\sim 3\%$ lower than required
 $f_{upper3dB}$ decreased to ~ 910.1 Hz, thus $GBW \approx 8.82$ MHz $\sim 11.8\%$ lower than required



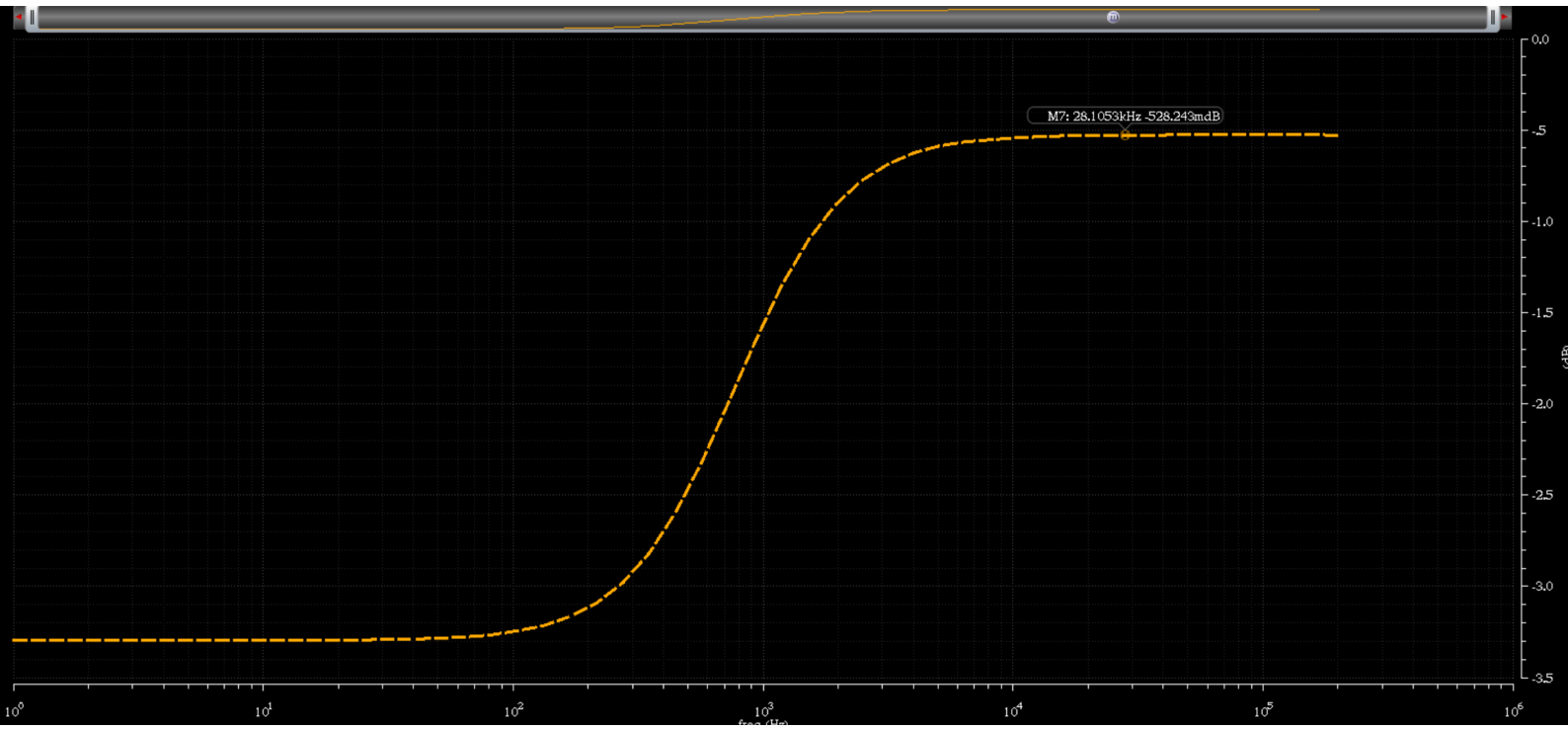
PM = ~ 63.1 degree as expected



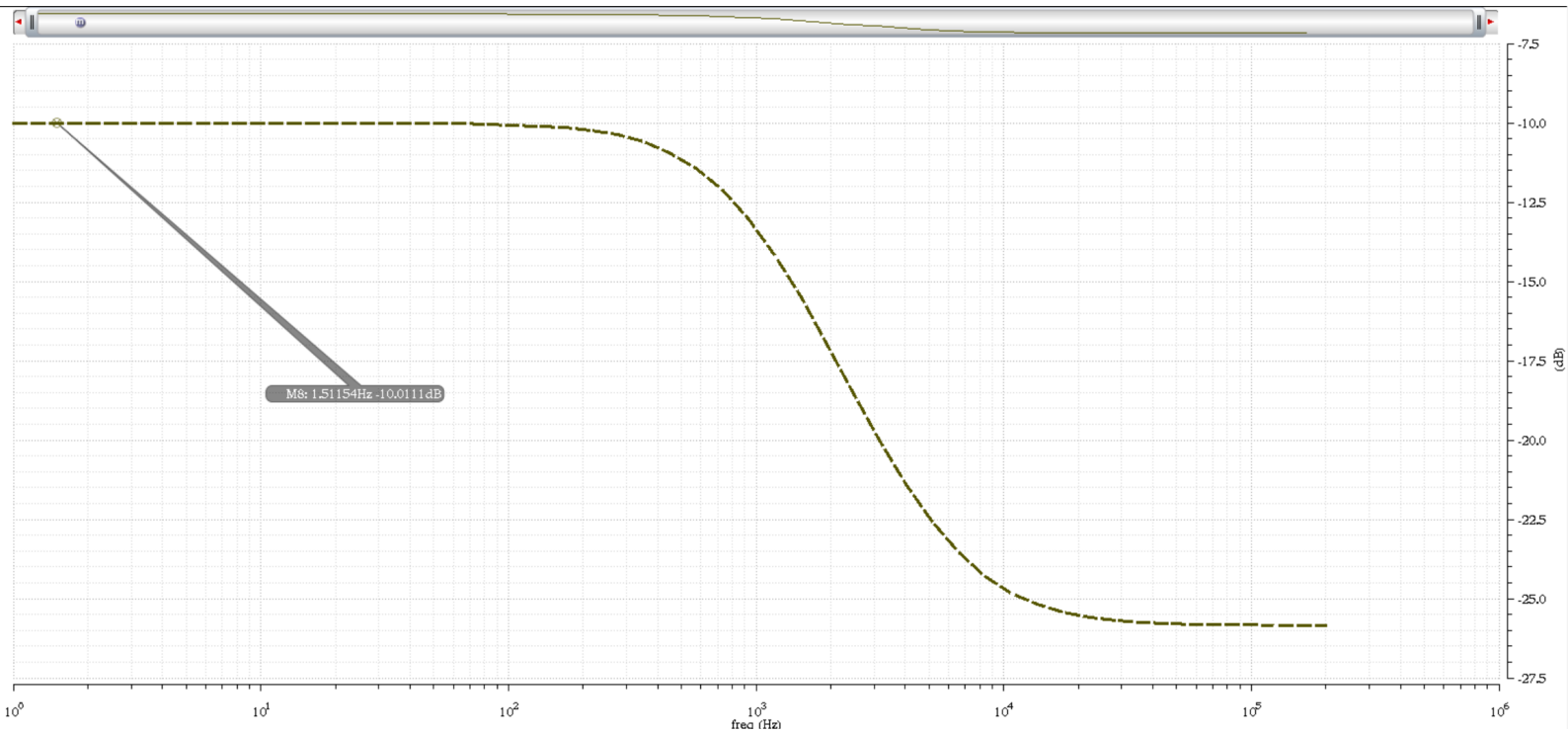
Slew rate decreased to $\sim 5.23 \text{ V}/\mu\text{s}$, still 4.6% higher than required.



I was able to obtain $\sim 2.5\text{V}$ output voltage swing



$A_{dd} \approx -0.528 \text{ dB}$ thus $PSRR_{V_{dd}} \approx 80.256 \text{ dB}$, more than double of required

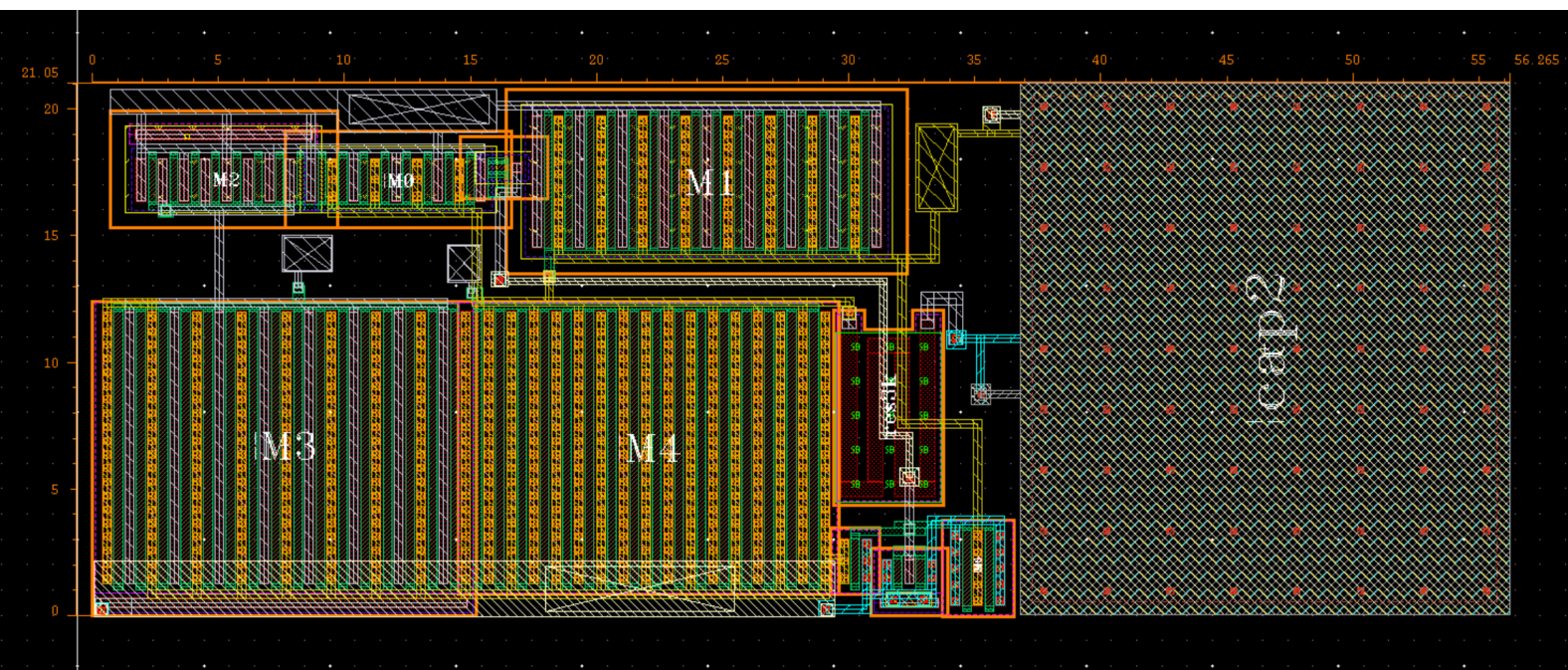


$A_{ss} \approx -10.01 \text{ dB}$ thus $PSRR_{V_{ss}} \approx 89.73 \text{ dB}$, more than double of required

Conclusion (After First Layout):

With two stage op-amp we were able to obtain very high gain ($\sim 80\text{dB}$) with bandwidth of $\sim 900\text{Hz}$. Size of resulting amplifier is roughly 30×62.3 . It is huge due to large sized transistors (M1, M3, M4 in layout) and compensation capacitor. Width (62.3 one) can be made smaller by squeezing components between M4 and capacitor. On the other hand my op-amp draws even less current than schematic, resulting $P_{\text{tot}} \approx 266 \mu\text{W}$, without violating slew rate requirement ($\text{SR} \approx 5.23 \text{ V}/\mu\text{s}$). My op-amp provides even better power supply rejection ratio for both V_{dd} and V_{ss} , $\sim 80\text{dB}$ and $\sim 90\text{dB}$ respectively. Voltage swing ($\sim 2.5 \text{ V}$) won't change between layout and schematic, even through V_{outDC} increased $\sim 0.4\text{V}$. Between layout and schematic all values are changed. But still only two specifications are not satisfied gain (3% lower) and GBW ($\sim 11\%$ lower).

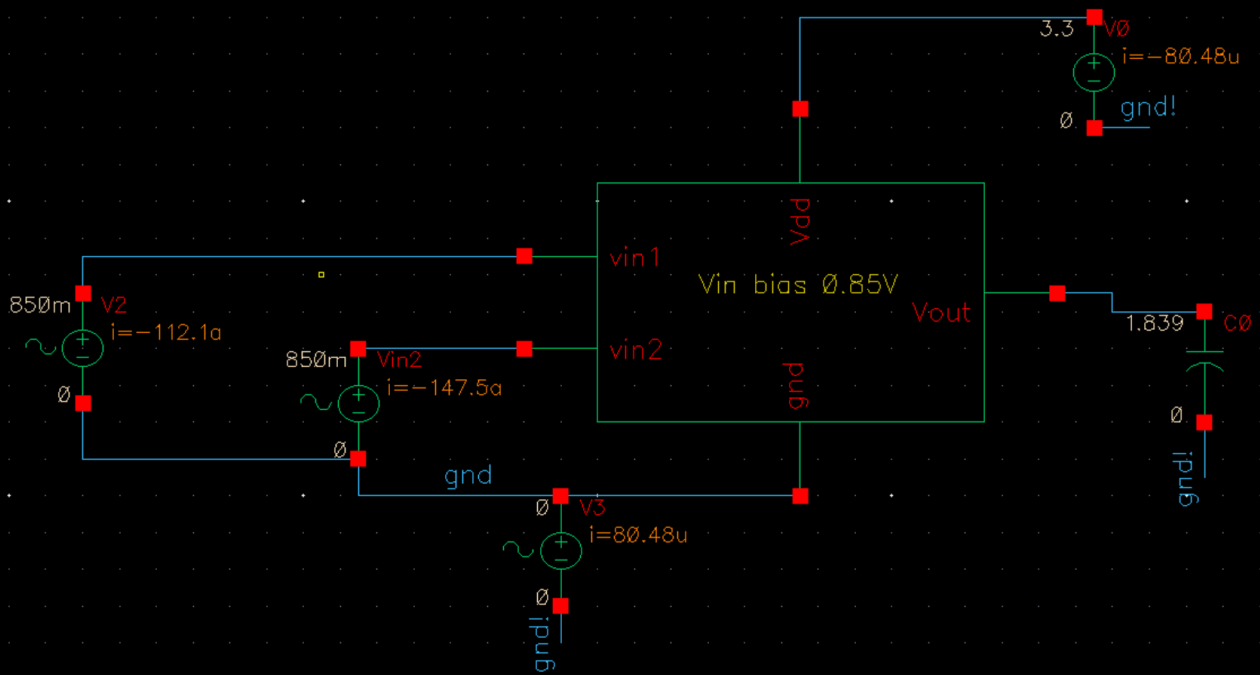
Final Layout



I was able to fit my design in to 21.05×56.265 rectangle, $\sim 36.56\%$ smaller than my initial layout.

DRC, LVS and QRC (Final)

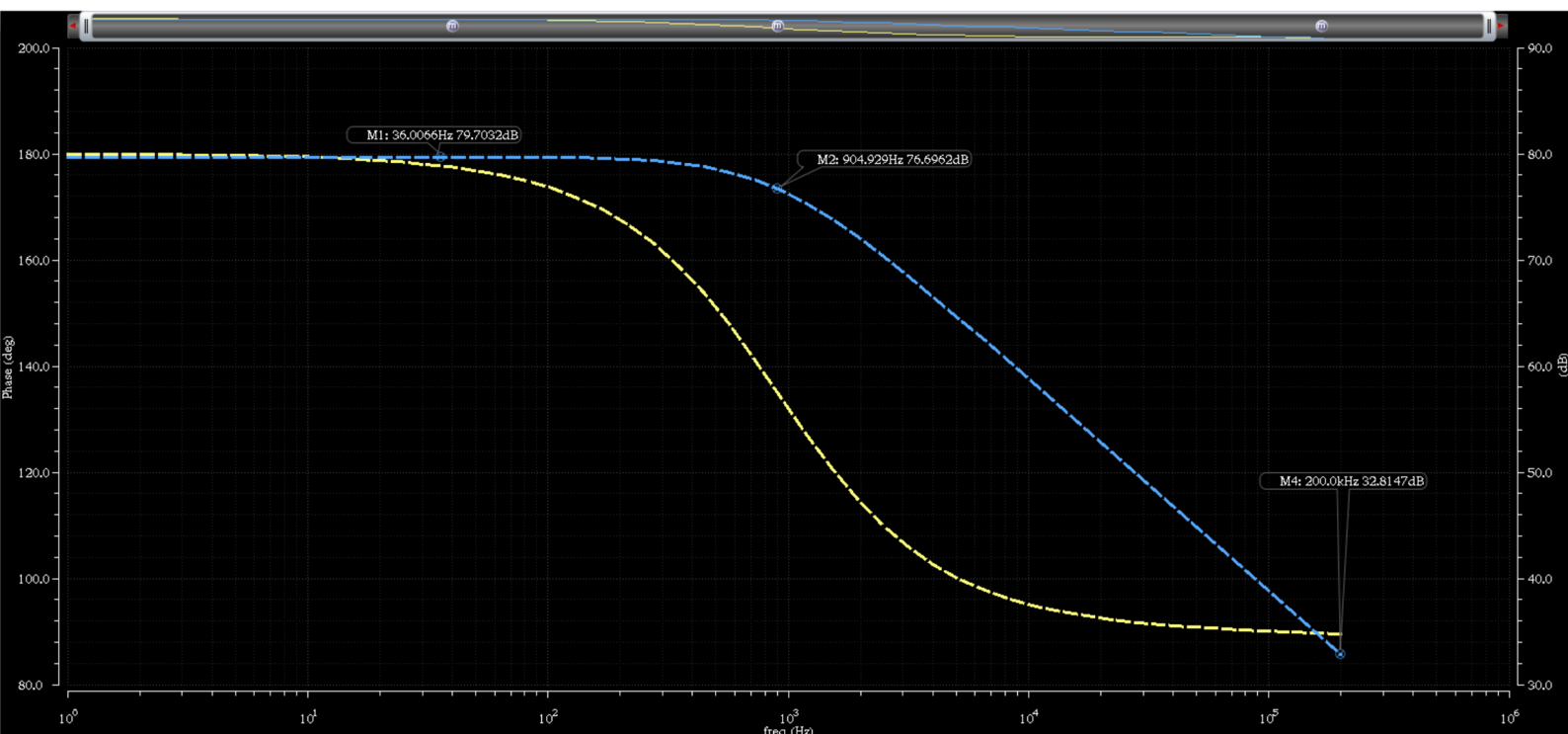




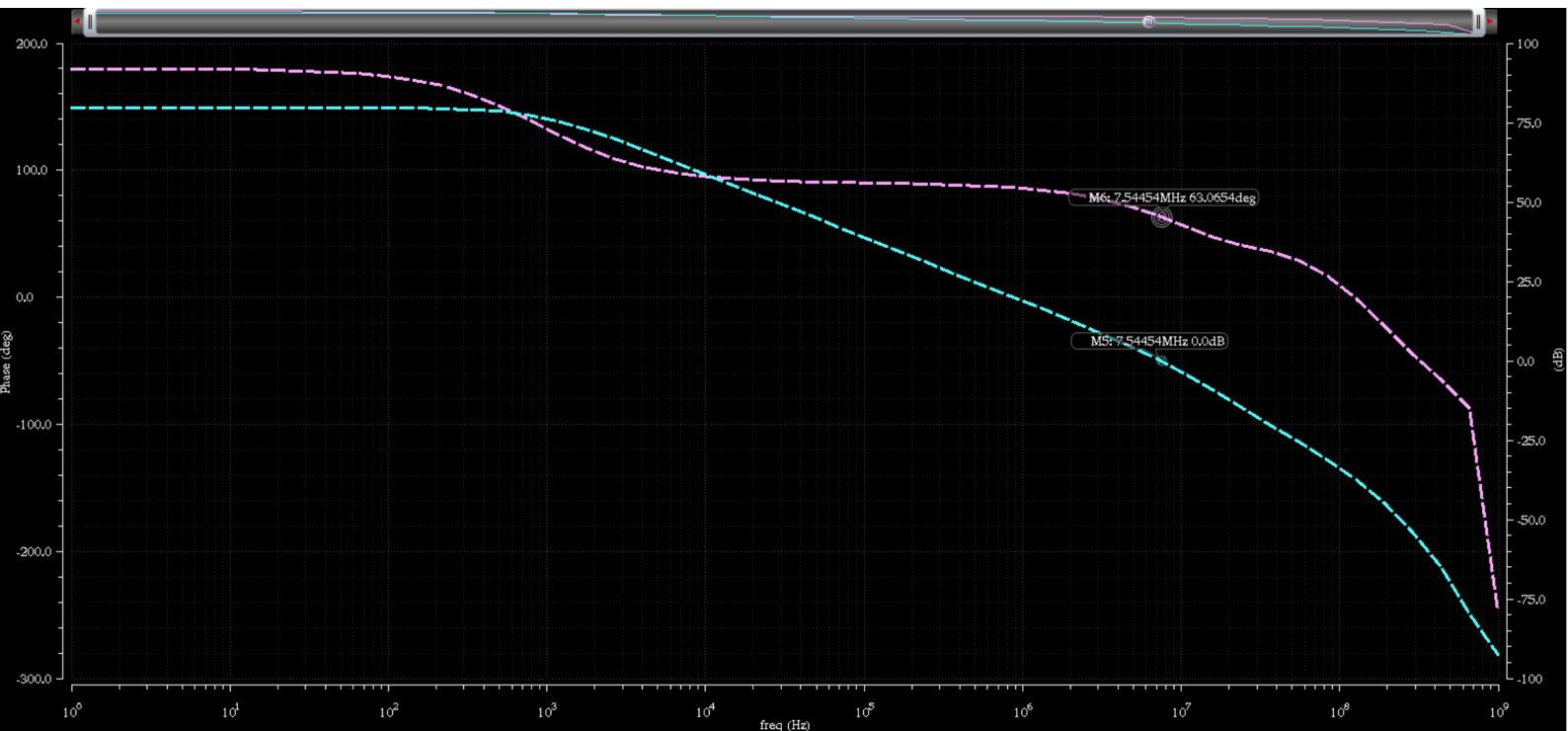
I_{tot} is decreased a little resulting $P_{\text{tot}} \approx 265.6 \mu\text{W}$

V_{outDC} increased even more, to $\sim 1.84 \text{ V}$

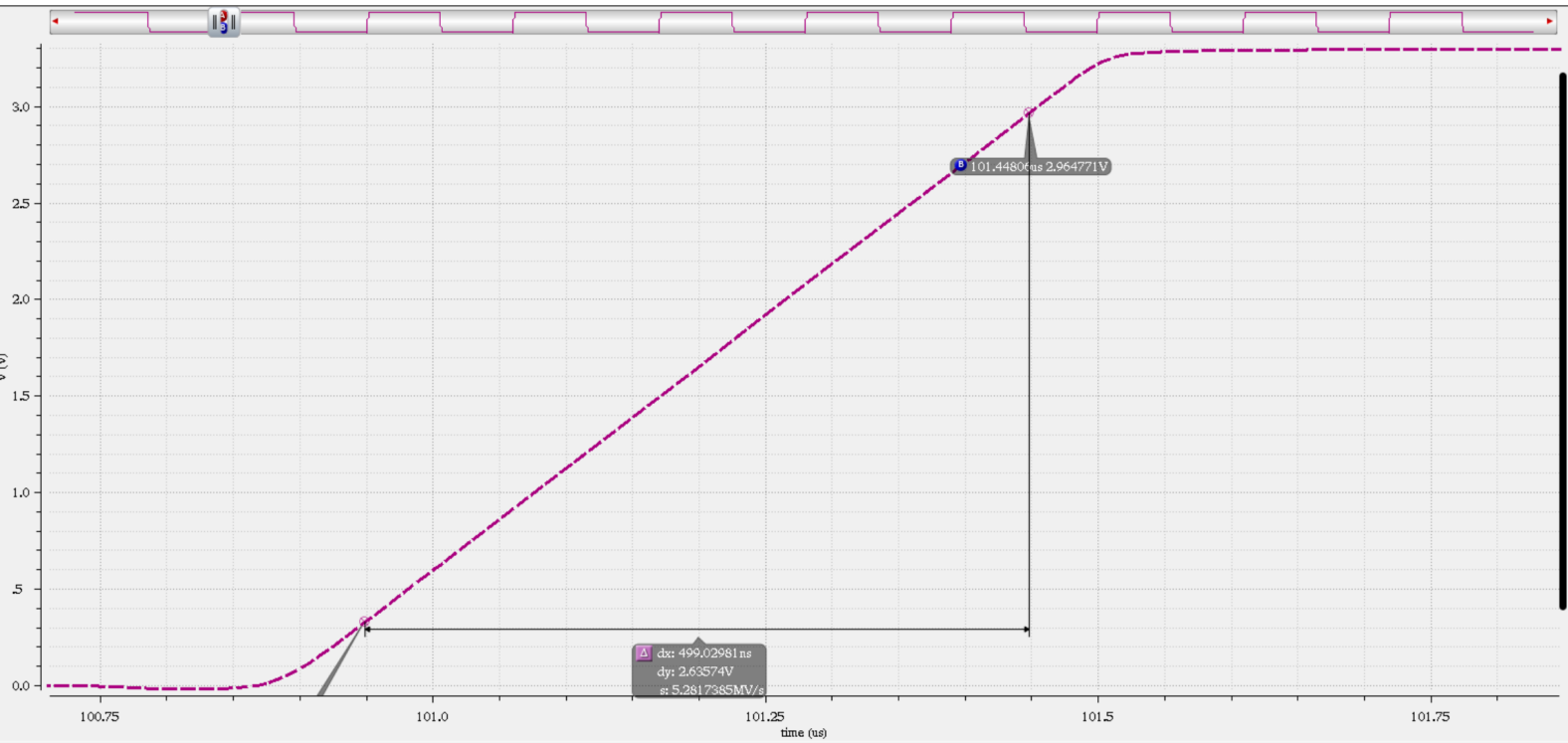
Simulation Results (After First Layout)



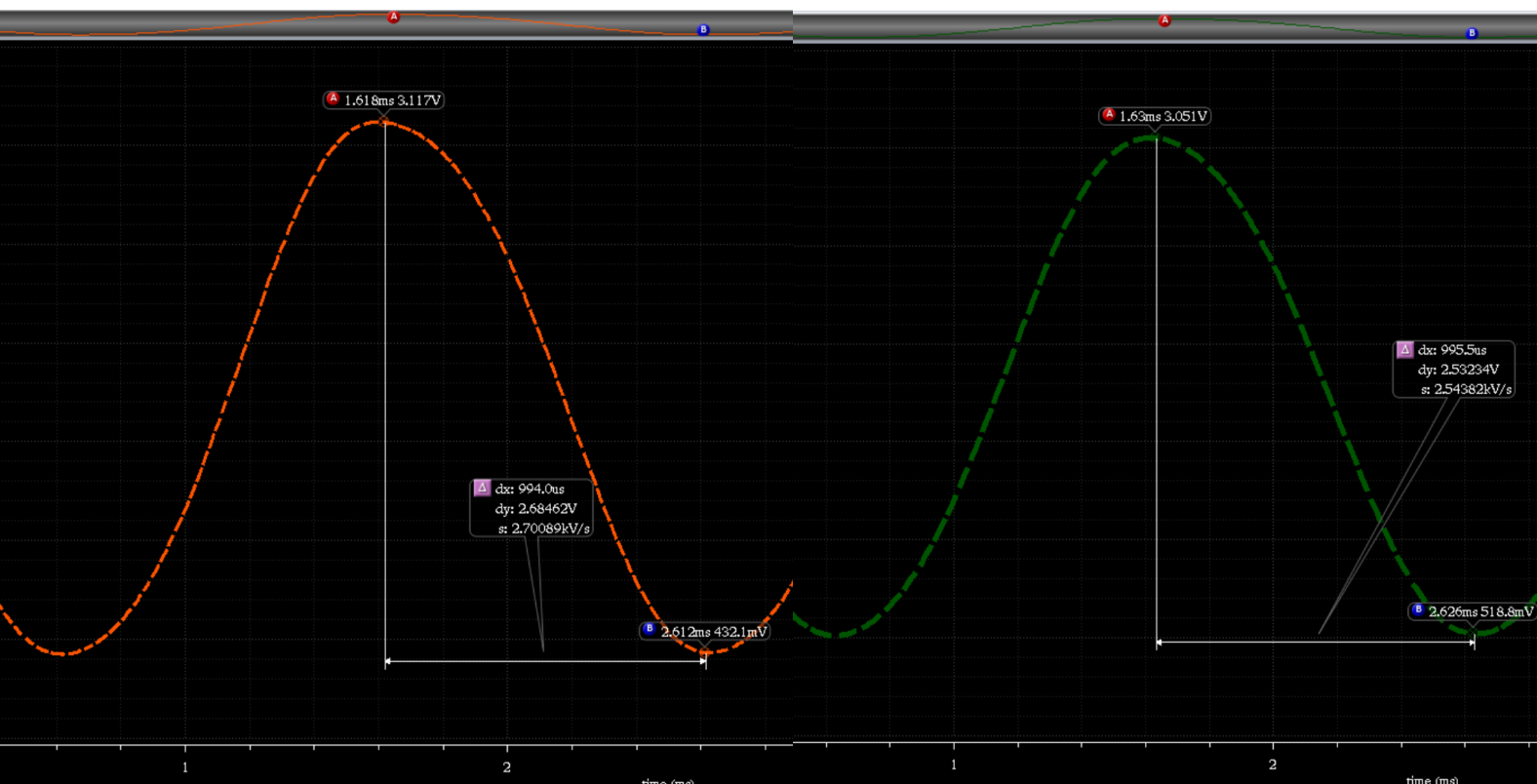
A_v decreased even more, to ~ 79.70 dB, ~ 9660.5 V/V which is $\sim 3.4\%$ lower than required
 $f_{upper3dB}$ decreased to ~ 904.9 Hz, thus $GBW \approx 8.74$ MHz $\sim 12.6\%$ lower than required



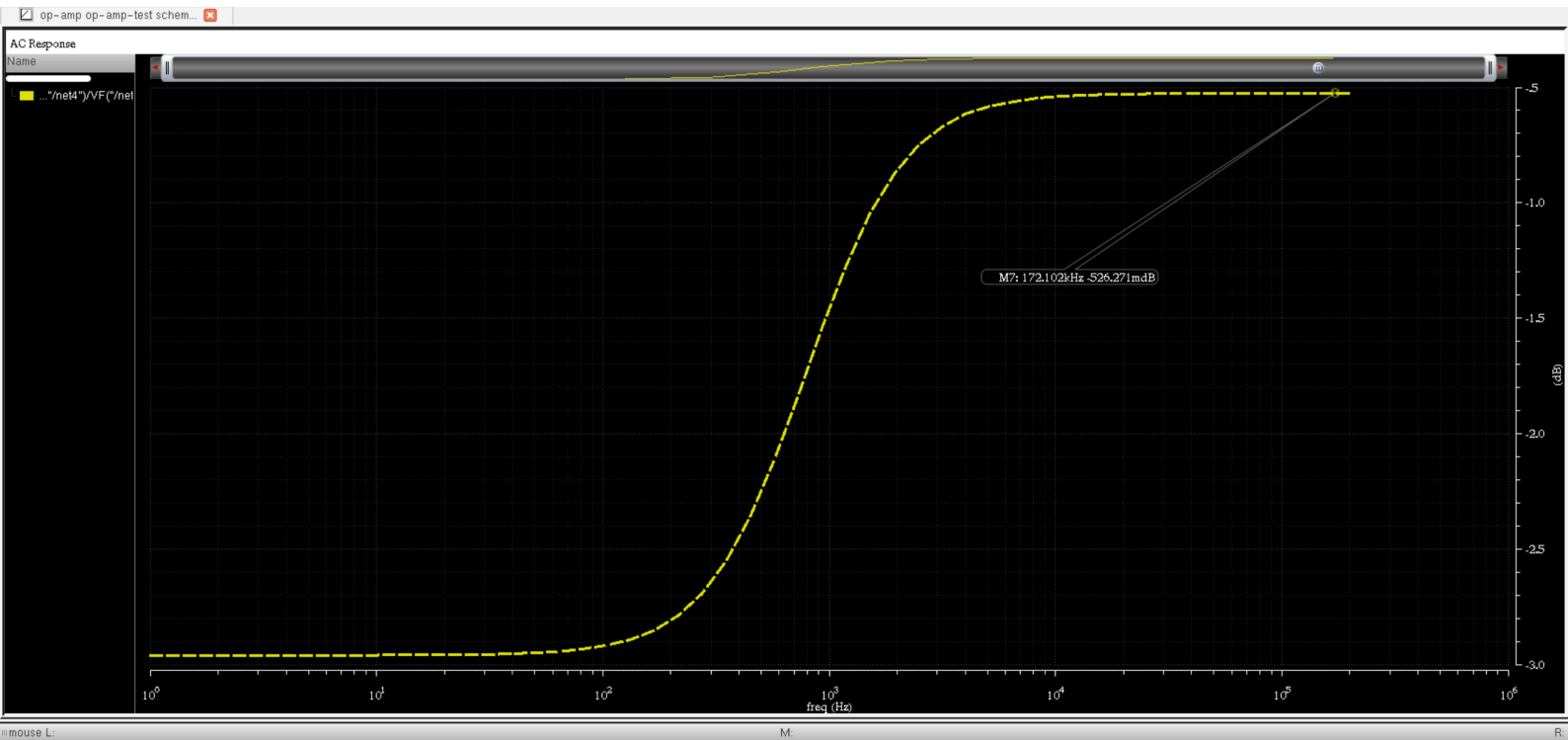
$PM \approx 63.1$ deg



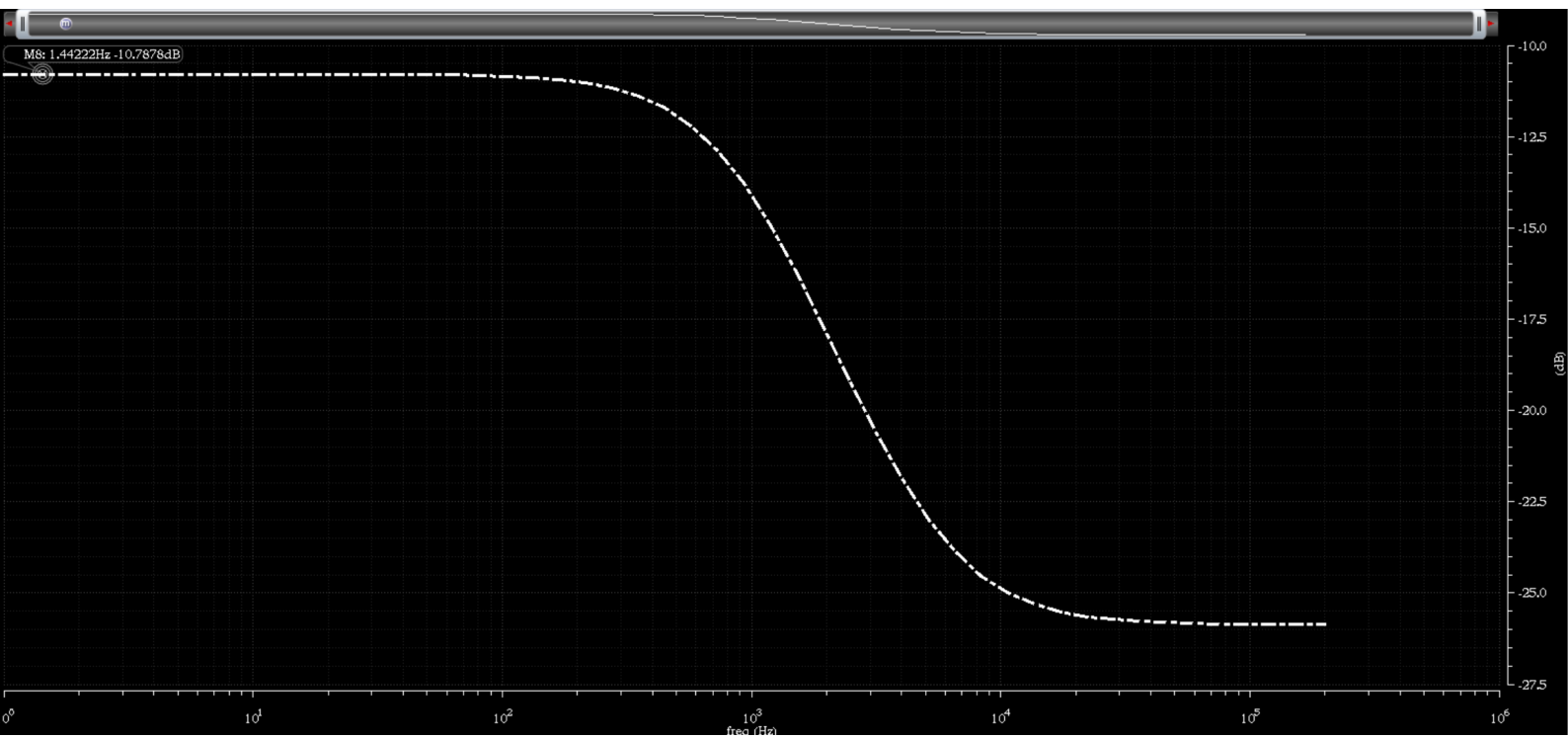
Slew rate ≈ 5.28 , increased a little compared to first layout



I was able to obtain $\sim 2.5V$ output voltage swing



$A_{dd} \approx -0.526 \text{ dB}$ thus $PSRR_{V_{dd}} \approx 80.229 \text{ dB}$, more than double of required



$A_{ss} \approx -10.78 \text{ dB}$ thus $PSRR_{V_{ss}} \approx 90.49 \text{ dB}$, more than double of required

Conclusion (Final):

I was able to reduce area of my amplifier by 36%, however my gain and gain-bandwidth got worse. My gain is still roughly 3% lower than required and my gain-bandwidth is roughly 13% lower than required, which is too low. I was able to decrease power consumption and increase slew rate at the same time. My PSRR values changed opposite direction, for V_{ss} (ground) increased for V_{dd} decreased. I was able to obtain similar output voltage swing as my first layout.